

# SSM6L11TU

## High Speed Switching Applications

- Optimum for high-density mounting in small packages
- Low ON-resistance Q1:  $R_{DS(ON)} = 395m\Omega$  (max) (@ $V_{GS} = 1.8V$ )  
Q2:  $R_{DS(ON)} = 430m\Omega$  (max) (@ $V_{GS} = -2.5V$ )

### Q1 Absolute Maximum Ratings ( $T_a = 25^\circ C$ )

Characteristics		Symbol	Rating	Unit
Drain-source voltage		$V_{DS}$	20	V
Gate-source voltage		$V_{GSS}$	$\pm 12$	V
Drain current	DC	$I_D$	0.5	A
	Pulse	$I_{DP}$	1.5	

### Q2 Absolute Maximum Ratings ( $T_a = 25^\circ C$ )

Characteristics		Symbol	Rating	Unit
Drain-source voltage		$V_{DS}$	-20	V
Gate-source voltage		$V_{GSS}$	$\pm 12$	V
Drain current	DC	$I_D$	-0.5	A
	Pulse	$I_{DP}$	-1.5	

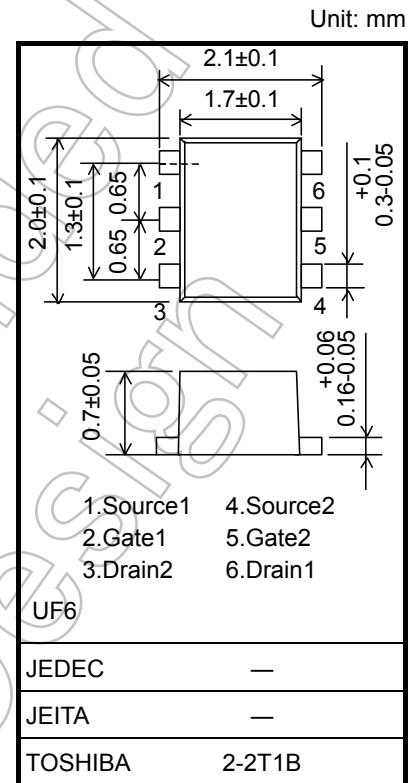
### Absolute Maximum Ratings (Q1,Q2 Common) ( $T_a = 25^\circ C$ )

Characteristics	Symbol	Rating	Unit
Drain power dissipation	$P_D$ (Note 1)	500	mW
Channel temperature	$T_{ch}$	150	$^\circ C$
Storage temperature range	$T_{stg}$	-55 to 150	$^\circ C$

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

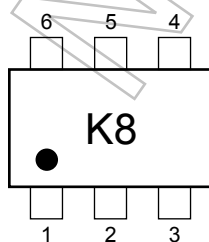
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Mounted on FR4 board. (total dissipation)  
( $25.4\text{ mm} \times 25.4\text{ mm} \times 1.6\text{ t}$ , Cu Pad:  $645\text{ mm}^2$ )

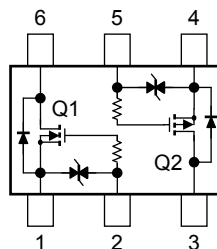


Weight: 7.0 mg (typ.)

### Marking



### Equivalent Circuit (top view)



Start of commercial production  
2004-03

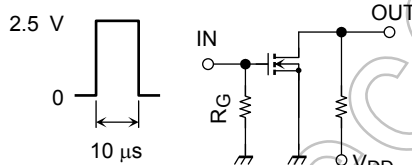
## Q1 Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current	$I_{GSS}$	$V_{GS} = \pm 12V, V_{DS} = 0$	—	—	$\pm 1$	$\mu A$
Drain-source breakdown voltage	$V_{(BR)DSS}$	$I_D = 1 mA, V_{GS} = 0$	20	—	—	V
	$V_{(BR)DSX}$	$I_D = 1 mA, V_{GS} = -12 V$	10	—	—	
Drain cut-off current	$I_{DSS}$	$V_{DS} = 20 V, V_{GS} = 0$	—	—	1	$\mu A$
Gate threshold voltage	$V_{th}$	$V_{DS} = 3 V, I_D = 0.1 mA$	0.5	—	1.1	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 3 V, I_D = 0.25 A$ (Note2)	1.2	2.4	—	S
Drain-source on-resistance	$R_{DS(ON)}$	$I_D = 0.25 A, V_{GS} = 4.0 V$ (Note2)	—	125	145	m $\Omega$
		$I_D = 0.25 A, V_{GS} = 2.5 V$ (Note2)	—	150	190	
		$I_D = 0.25 A, V_{GS} = 1.8 V$ (Note2)	—	200	395	
Input capacitance	$C_{iss}$	$V_{DS} = 10 V, V_{GS} = 0, f = 1 MHz$	—	268	—	pF
Reverse transfer capacitance	$C_{rss}$	$V_{DS} = 10 V, V_{GS} = 0, f = 1 MHz$	—	34	—	pF
Output capacitance	$C_{oss}$	$V_{DS} = 10 V, V_{GS} = 0, f = 1 MHz$	—	44	—	pF
Switching time	Turn-on time	$t_{on}$	—	11	—	ns
	Turn-off time	$t_{off}$	—	15	—	

Note2: Pulse test

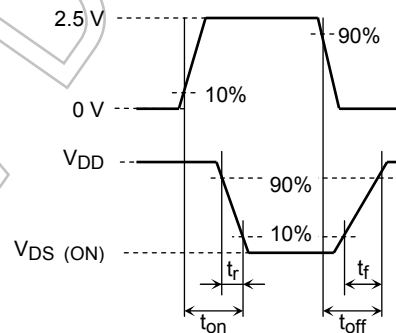
## Switching Time Test Circuit

### (a) Test Circuit

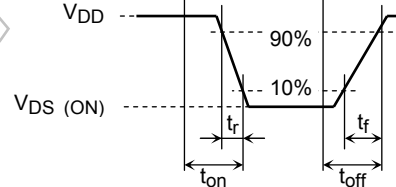


$V_{DD} = 10 V$   
 $R_G = 4.7 \Omega$   
 Duty  $\leq 1\%$   
 $V_{IN}$ :  $t_r, t_f < 5 ns$   
 Common Source  
 $T_a = 25^\circ C$

### (b) $V_{IN}$



### (c) $V_{OUT}$



## Precaution

$V_{th}$  can be expressed as the voltage between gate and source when the low operating current value is  $I_D = 100 \mu A$  for this product. For normal switching operation,  $V_{GS(ON)}$  requires a higher voltage than  $V_{th}$  and  $V_{GS(OFF)}$  requires a lower voltage than  $V_{th}$ .

(The relationship can be established as follows:  $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$ )

Please take this into consideration when using the device.

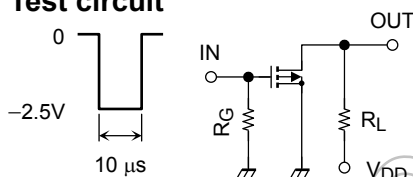
**Q2 Electrical Characteristics (Ta = 25°C)**

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current	$I_{GSS}$	$V_{GS} = \pm 12V, V_{DS} = 0$	—	—	$\pm 1$	$\mu A$
Drain-source breakdown voltage	$V_{(BR)DSS}$	$I_D = -1 mA, V_{GS} = 0$	-20	—	—	V
	$V_{(BR)DSX}$	$I_D = -1 mA, V_{GS} = +12 V$	-8	—	—	
Drain cut-off current	$I_{DSS}$	$V_{DS} = -20 V, V_{GS} = 0$	—	—	-1	$\mu A$
Gate threshold voltage	$V_{th}$	$V_{DS} = -3 V, I_D = -0.1 mA$	-0.5	—	-1.1	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = -3 V, I_D = -0.25 A$ (Note3)	0.65	1.3	—	S
Drain-source on-resistance	$R_{DS(ON)}$	$I_D = -0.25 A, V_{GS} = -4 V$ (Note3)	—	210	260	m $\Omega$
		$I_D = -0.25 A, V_{GS} = -2.5 V$ (Note3)	—	310	430	
Input capacitance	$C_{iss}$	$V_{DS} = -10 V, V_{GS} = 0, f = 1 MHz$	—	218	—	pF
Reverse transfer capacitance	$C_{rss}$	$V_{DS} = -10 V, V_{GS} = 0, f = 1 MHz$	—	42	—	pF
Output capacitance	$C_{oss}$	$V_{DS} = -10 V, V_{GS} = 0, f = 1 MHz$	—	52	—	pF
Switching time	Turn-on time	$t_{on}$	$V_{DD} = -10 V, I_D = -0.25 A,$	—	16	ns
	Turn-off time	$t_{off}$	$V_{GS} = 0 \text{ to } -2.5 V, R_G = 4.7 \Omega$	—	15	

Note3: Pulse test

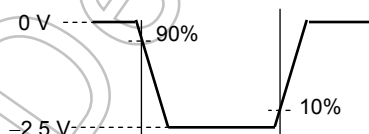
**Switching Time Test Circuit**

(a) Test circuit

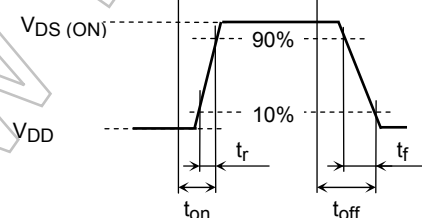


$V_{DD} = -10 V$   
 $R_G = 4.7 \Omega$   
 Duty  $\leq 1\%$   
 $V_{IN}$ :  $t_r, t_f < 5 ns$   
 Common Source  
 $T_a = 25^\circ C$

(b)  $V_{IN}$



(c)  $V_{OUT}$



**Precaution**

$V_{th}$  can be expressed as the voltage between gate and source when the low operating current value is  $I_D = -100 \mu A$  for this product. For normal switching operation,  $V_{GS(on)}$  requires a higher voltage than  $V_{th}$  and  $V_{GS(off)}$  requires a lower voltage than  $V_{th}$ .

(The relationship can be established as follows:  $V_{GS(off)} < V_{th} < V_{GS(on)}$ )

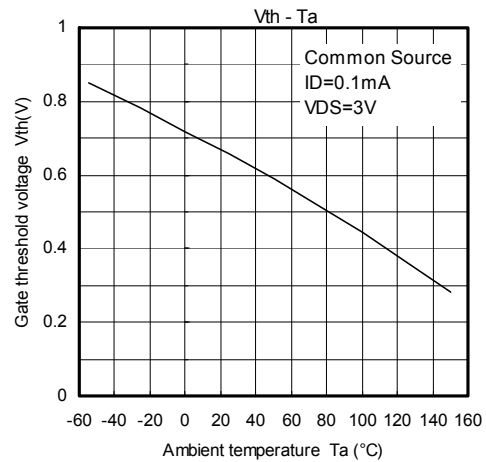
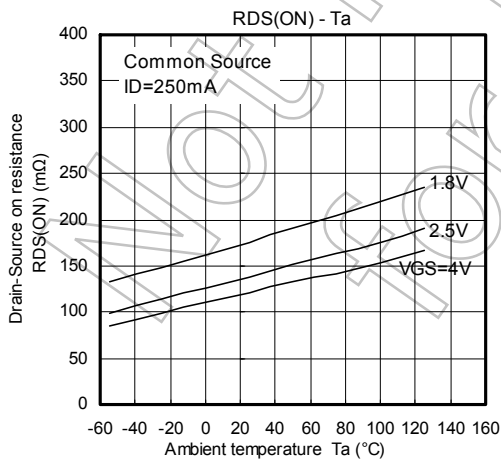
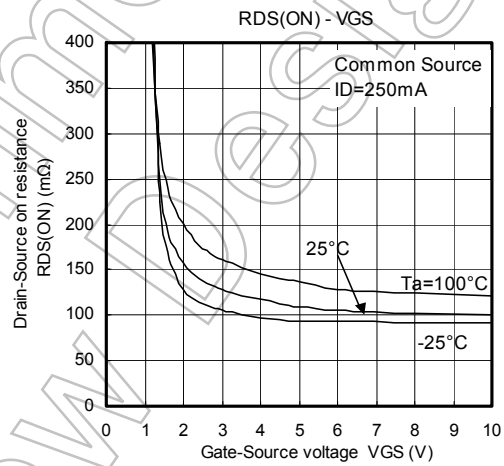
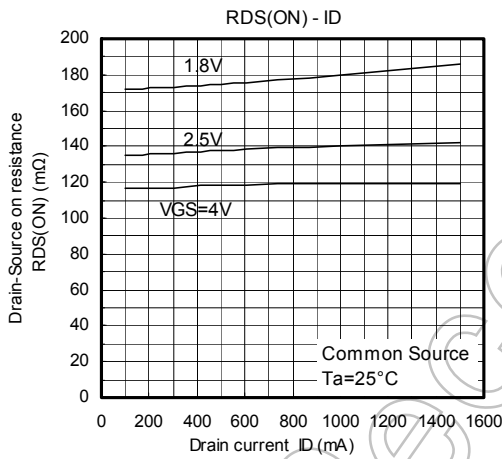
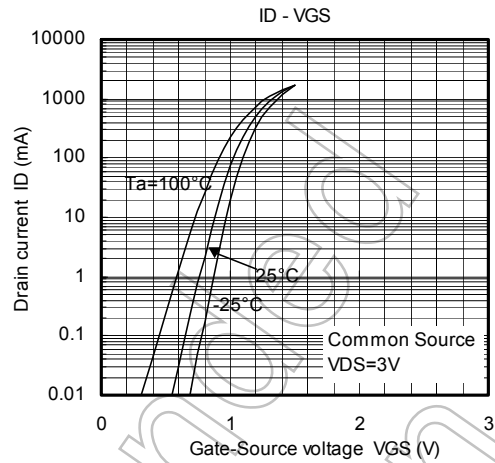
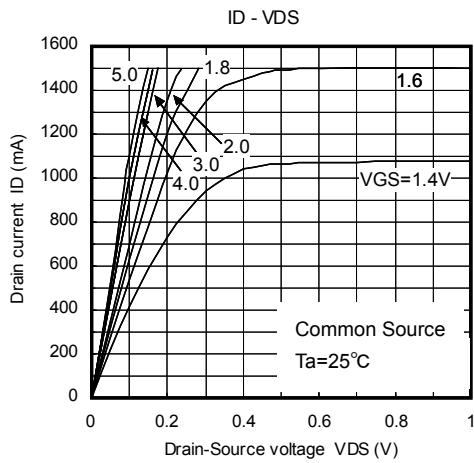
Please take this into consideration when using the device.

**Handling Precaution**

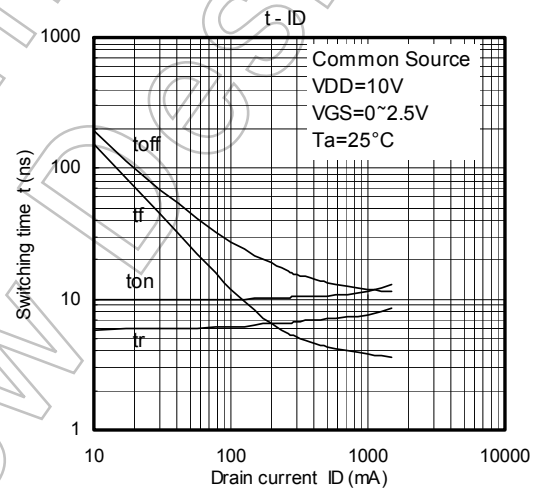
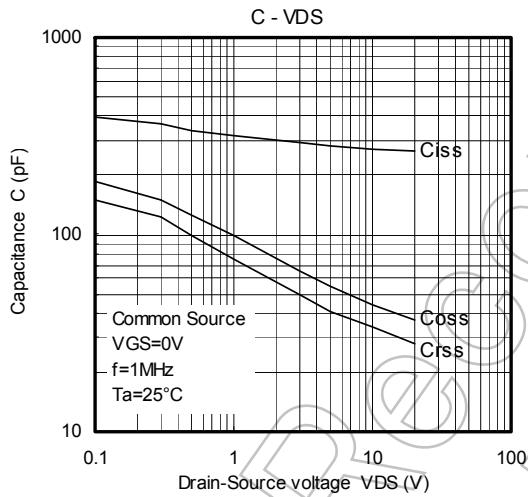
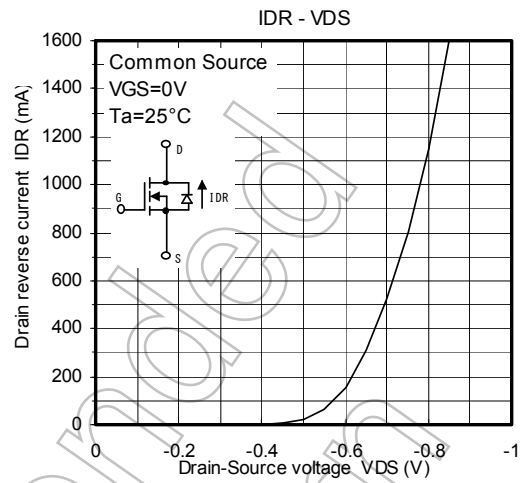
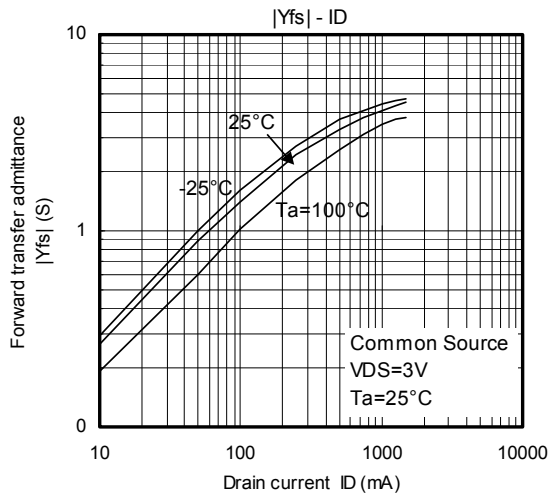
When handling individual devices (which are not yet mounted on a circuit board), be sure that the environment is protected against electrostatic electricity. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.

Thermal resistance  $R_{th(j-a)}$  and drain power dissipation  $P_D$  vary depending on board material, board area, board thickness and pad area. When using this device, please take heat dissipation into consideration.

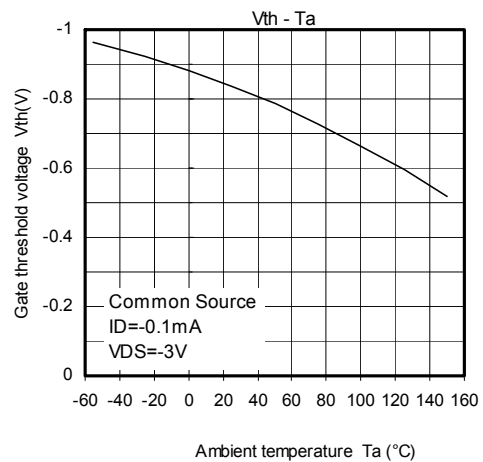
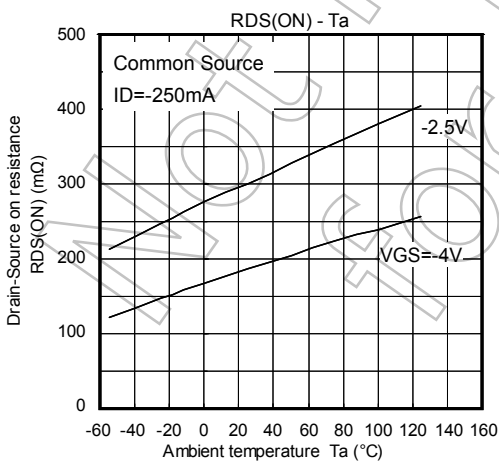
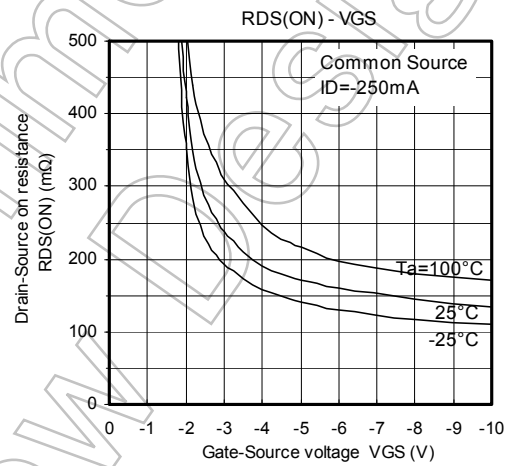
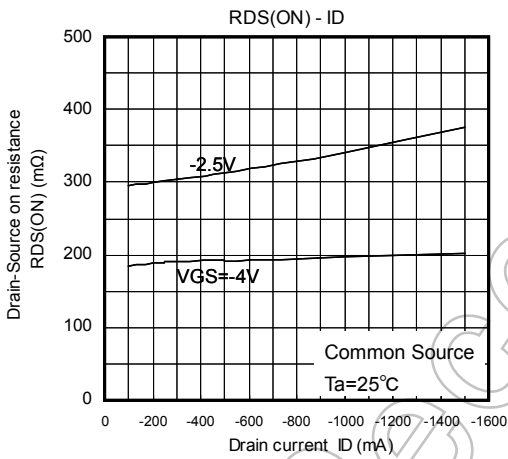
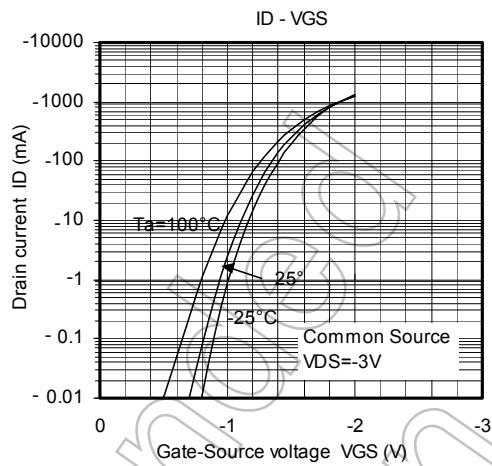
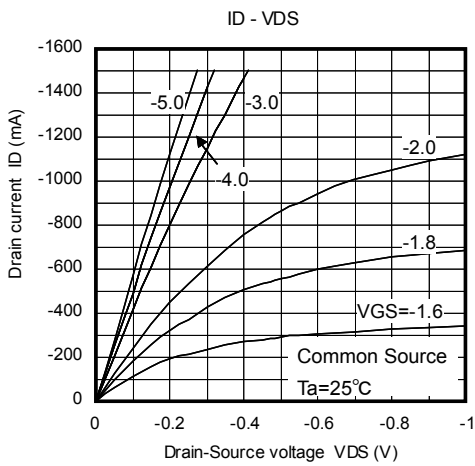
Q1(Nch MOS FET)



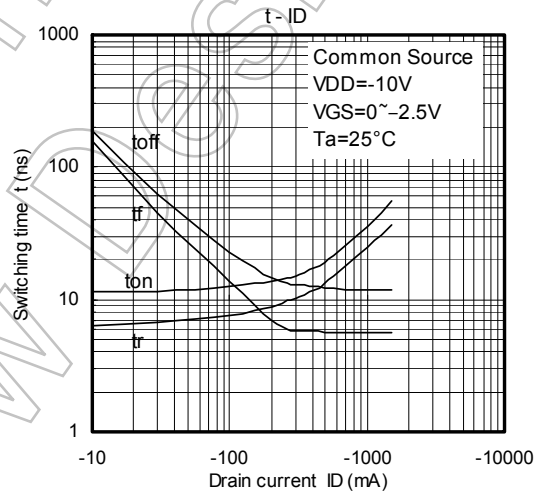
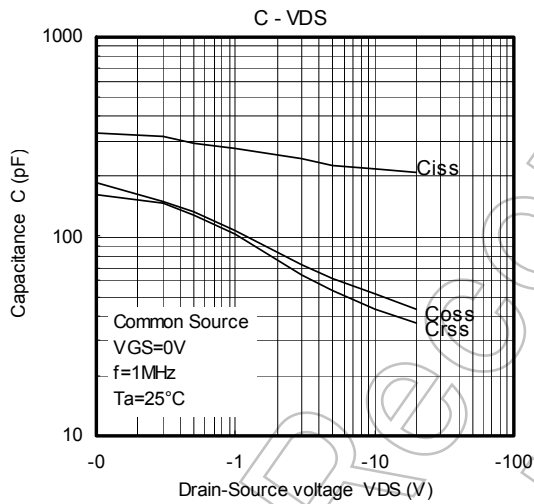
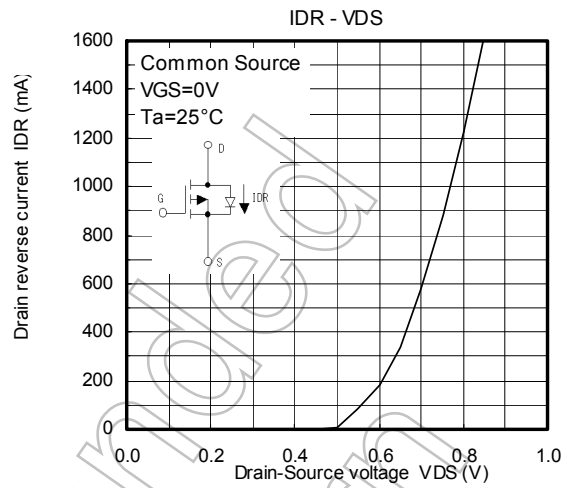
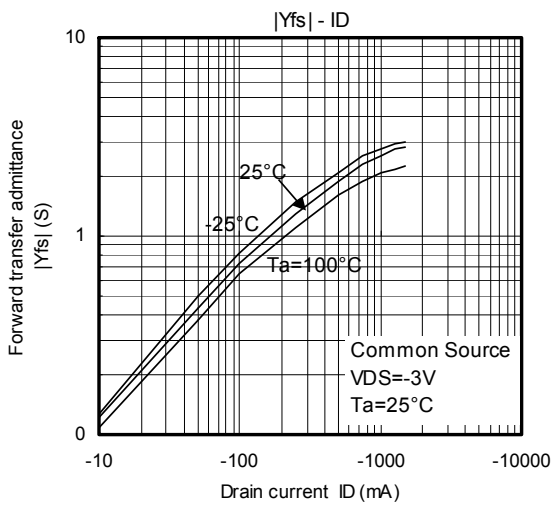
**Q1(Nch MOS FET)**

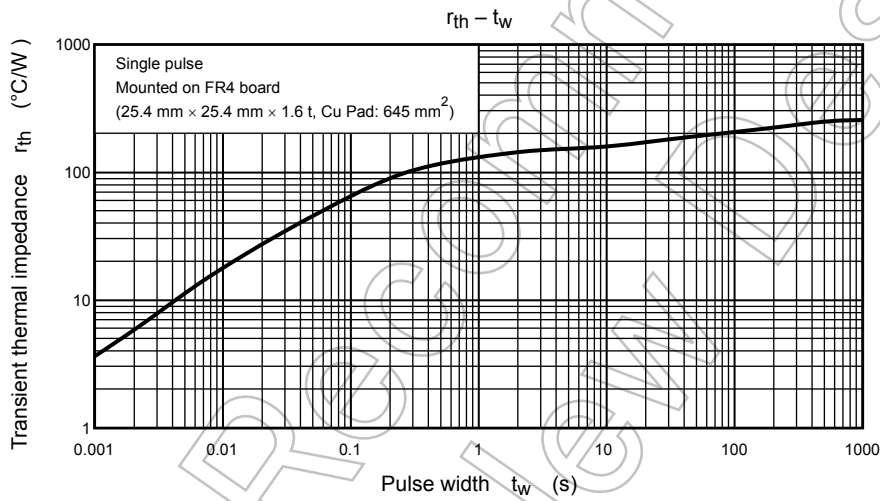
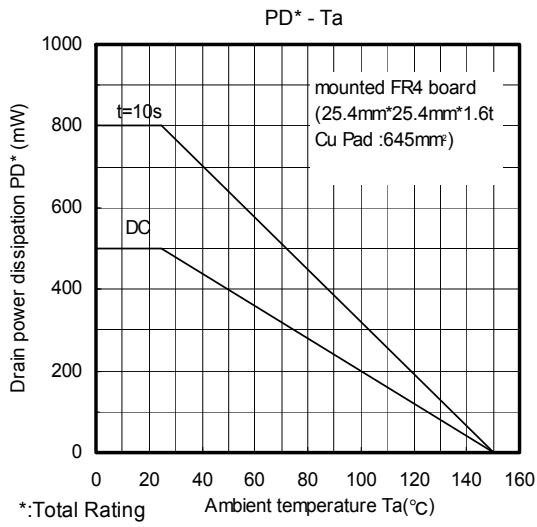


**Q2(Pch MOS FET)**



**Q2(Pch MOS FET)**







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